

Thyristor \ Diode Module

$$V_{RRM} = 2 \times 1200 \text{ V}$$

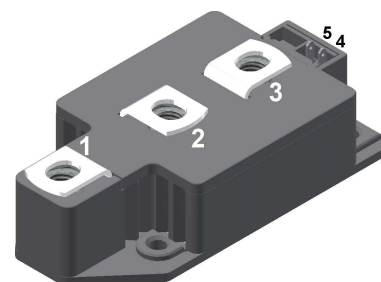
$$I_{TAV} = 320 \text{ A}$$

$$V_T = 1.08 \text{ V}$$

Phase leg

Part number

MCD310-12io1



Backside: isolated

 E72873



Features / Advantages:

- Thyristor for line frequency
- Planar passivated chip
- Long-term stability
- Direct Copper Bonded Al₂O₃-ceramic

Applications:

- Line rectifying 50/60 Hz
- Softstart AC motor control
- DC Motor control
- Power converter
- AC power control
- Lighting and temperature control

Package: Y2

- Isolation Voltage: 3600 V~
- Industry standard outline
- RoHS compliant
- Soldering pins for PCB mounting
- Base plate: DCB ceramic
- Reduced weight
- Advanced power cycling

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Rectifier				Ratings			
Symbol	Definition	Conditions		min.	typ.	max.	Unit
$V_{RSM/DSM}$	max. non-repetitive reverse/forward blocking voltage	$T_{VJ} = 25^{\circ}\text{C}$				1300	V
$V_{RRM/DRM}$	max. repetitive reverse/forward blocking voltage	$T_{VJ} = 25^{\circ}\text{C}$				1200	V
$I_{R/D}$	reverse current, drain current	$V_{R/D} = 1200\text{ V}$	$T_{VJ} = 25^{\circ}\text{C}$			1	mA
		$V_{R/D} = 1200\text{ V}$	$T_{VJ} = 140^{\circ}\text{C}$			40	mA
V_T	forward voltage drop	$I_T = 300\text{ A}$	$T_{VJ} = 25^{\circ}\text{C}$			1.14	V
		$I_T = 600\text{ A}$				1.32	V
		$I_T = 300\text{ A}$	$T_{VJ} = 125^{\circ}\text{C}$			1.08	V
		$I_T = 600\text{ A}$				1.30	V
I_{TAV}	average forward current	$T_C = 85^{\circ}\text{C}$	$T_{VJ} = 140^{\circ}\text{C}$			320	A
$I_{T(RMS)}$	RMS forward current	180° sine				500	A
V_{T0}	threshold voltage	} for power loss calculation only	$T_{VJ} = 140^{\circ}\text{C}$			0.80	V
r_T	slope resistance					0.82	mΩ
R_{thJC}	thermal resistance junction to case					0.11	K/W
R_{thCH}	thermal resistance case to heatsink				0.04		K/W
P_{tot}	total power dissipation		$T_C = 25^{\circ}\text{C}$			1030	W
I_{TSM}	max. forward surge current	$t = 10\text{ ms}; (50\text{ Hz}), \text{ sine}$	$T_{VJ} = 45^{\circ}\text{C}$			9.20	kA
		$t = 8,3\text{ ms}; (60\text{ Hz}), \text{ sine}$	$V_R = 0\text{ V}$			9.94	kA
		$t = 10\text{ ms}; (50\text{ Hz}), \text{ sine}$	$T_{VJ} = 140^{\circ}\text{C}$			7.82	kA
		$t = 8,3\text{ ms}; (60\text{ Hz}), \text{ sine}$	$V_R = 0\text{ V}$			8.45	kA
I^2t	value for fusing	$t = 10\text{ ms}; (50\text{ Hz}), \text{ sine}$	$T_{VJ} = 45^{\circ}\text{C}$			423.2	kA ² s
		$t = 8,3\text{ ms}; (60\text{ Hz}), \text{ sine}$	$V_R = 0\text{ V}$			410.6	kA ² s
		$t = 10\text{ ms}; (50\text{ Hz}), \text{ sine}$	$T_{VJ} = 140^{\circ}\text{C}$			305.8	kA ² s
		$t = 8,3\text{ ms}; (60\text{ Hz}), \text{ sine}$	$V_R = 0\text{ V}$			296.7	kA ² s
C_J	junction capacitance	$V_R = 400\text{ V}$ $f = 1\text{ MHz}$	$T_{VJ} = 25^{\circ}\text{C}$		438		pF
P_{GM}	max. gate power dissipation	$t_p = 30\text{ }\mu\text{s}$	$T_C = 140^{\circ}\text{C}$			120	W
		$t_p = 500\text{ }\mu\text{s}$				60	W
P_{GAV}	average gate power dissipation					20	W
$(di/dt)_{cr}$	critical rate of rise of current	$T_{VJ} = 140^{\circ}\text{C}; f = 50\text{ Hz}$ repetitive, $I_T = 960\text{ A}$				100	A/ μs
		$t_p = 200\text{ }\mu\text{s}; di_G/dt = 1\text{ A}/\mu\text{s};$ $I_G = 1\text{ A}; V = \frac{2}{3} V_{DRM}$ non-repet., $I_T = 320\text{ A}$				500	A/ μs
$(dv/dt)_{cr}$	critical rate of rise of voltage	$V = \frac{2}{3} V_{DRM}$	$T_{VJ} = 140^{\circ}\text{C}$			1000	V/ μs
		$R_{GK} = \infty$; method 1 (linear voltage rise)					
V_{GT}	gate trigger voltage	$V_D = 6\text{ V}$	$T_{VJ} = 25^{\circ}\text{C}$			2	V
			$T_{VJ} = -40^{\circ}\text{C}$			3	V
I_{GT}	gate trigger current	$V_D = 6\text{ V}$	$T_{VJ} = 25^{\circ}\text{C}$			150	mA
			$T_{VJ} = -40^{\circ}\text{C}$			200	mA
V_{GD}	gate non-trigger voltage	$V_D = \frac{2}{3} V_{DRM}$	$T_{VJ} = 140^{\circ}\text{C}$			0.25	V
I_{GD}	gate non-trigger current					10	mA
I_L	latching current	$t_p = 30\text{ }\mu\text{s}$	$T_{VJ} = 25^{\circ}\text{C}$			200	mA
		$I_G = 0.45\text{ A}; di_G/dt = 0.45\text{ A}/\mu\text{s}$					
I_H	holding current	$V_D = 6\text{ V}$ $R_{GK} = \infty$	$T_{VJ} = 25^{\circ}\text{C}$			150	mA
t_{gd}	gate controlled delay time	$V_D = \frac{1}{2} V_{DRM}$	$T_{VJ} = 25^{\circ}\text{C}$			2	μs
		$I_G = 1\text{ A}; di_G/dt = 1\text{ A}/\mu\text{s}$					
t_q	turn-off time	$V_R = 100\text{ V}; I_T = 320\text{ A}; V = \frac{2}{3} V_{DRM}$ $T_{VJ} = 125^{\circ}\text{C}$ $di/dt = 10\text{ A}/\mu\text{s}$ $dv/dt = 50\text{ V}/\mu\text{s}$ $t_p = 200\text{ }\mu\text{s}$			200		μs

Package Y2			Ratings			
Symbol	Definition	Conditions	min.	typ.	max.	Unit
I _{RMS}	RMS current	per terminal			600	A
T _{VJ}	virtual junction temperature		-40		140	°C
T _{op}	operation temperature		-40		125	°C
T _{stg}	storage temperature		-40		125	°C
Weight				255		g
M _D	mounting torque		2.5		5	Nm
M _T	terminal torque		12		15	Nm
d _{Spp/App}	creepage distance on surface striking distance through air	terminal to terminal	13.0			mm
d _{Spb/Apb}		terminal to backside	13.0			mm
V _{ISOL}	isolation voltage	t = 1 second	3600			V
		t = 1 minute	3000			V
			50/60 Hz, RMS; I _{ISOL} ≤ 1 mA			



Ordering	Ordering Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standard	MCD310-12io1	MCD310-12io1	Box	2	428787

Equivalent Circuits for Simulation

* on die level

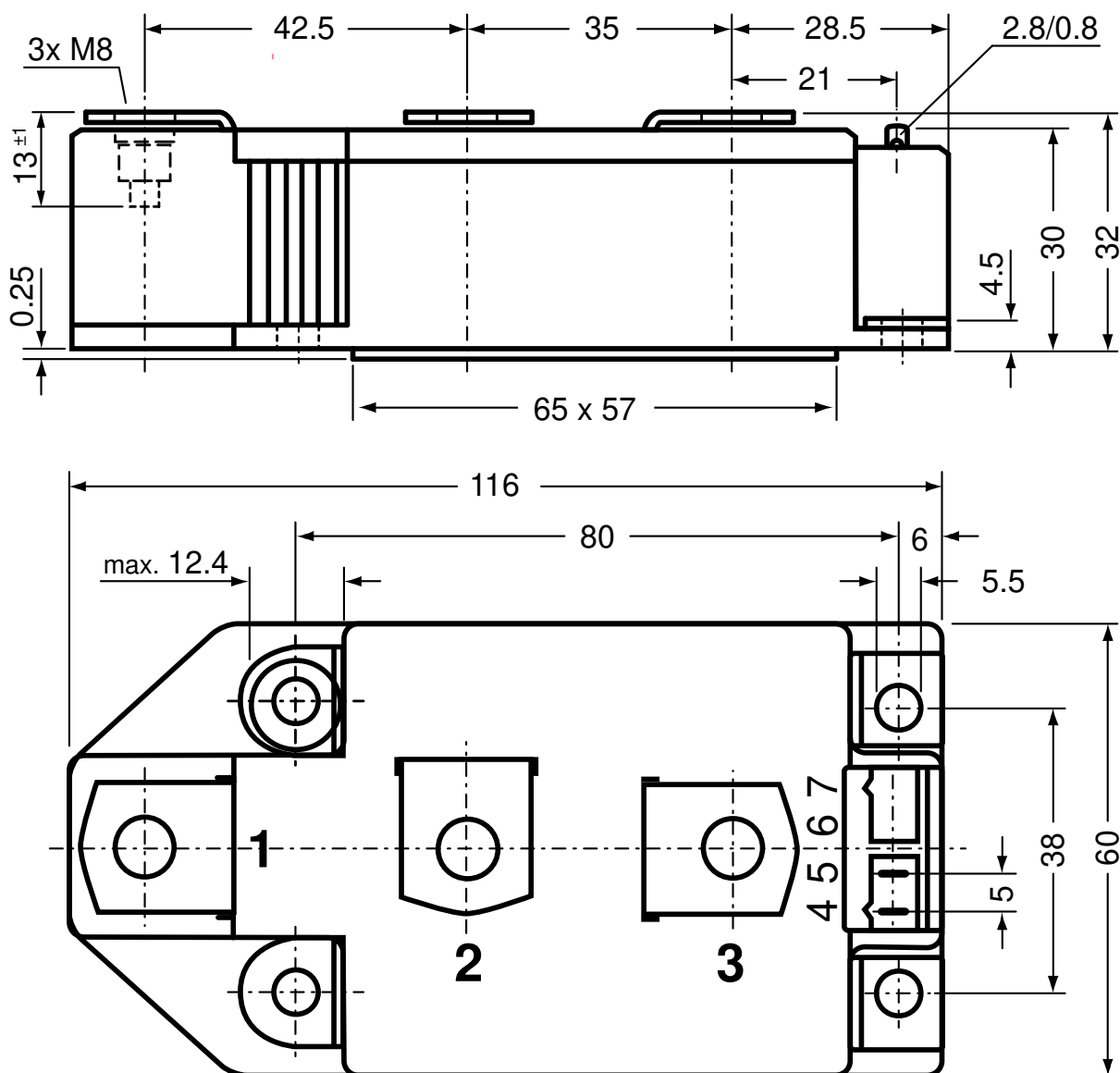
$T_{VJ} = 140^{\circ}\text{C}$



Thyristor

$V_{0\max}$	threshold voltage	0.8	V
$R_{0\max}$	slope resistance *	0.32	mΩ

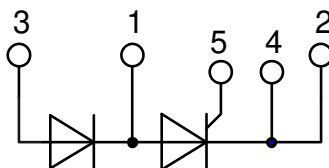
Outlines Y2



Optional accessories for modules

Keyed gate/cathode twin plugs with wire length = 350 mm, gate = white, cathode = red

Type ZY 180L (L = Left for pin pair 4/5) UL 758, style 3751



Thyristor


Fig. 1 Surge overload current
 $I_{T(F)SM}$: crest value, t: duration

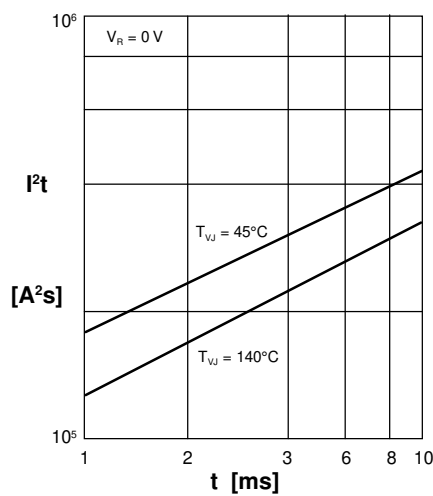


Fig. 2 I^2t versus time (1-10 ms)

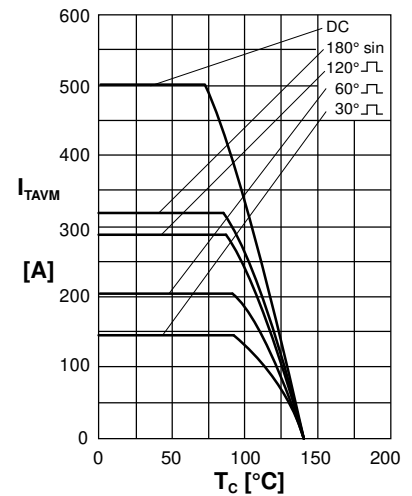


Fig. 3 Max. forward current
 at case temperature

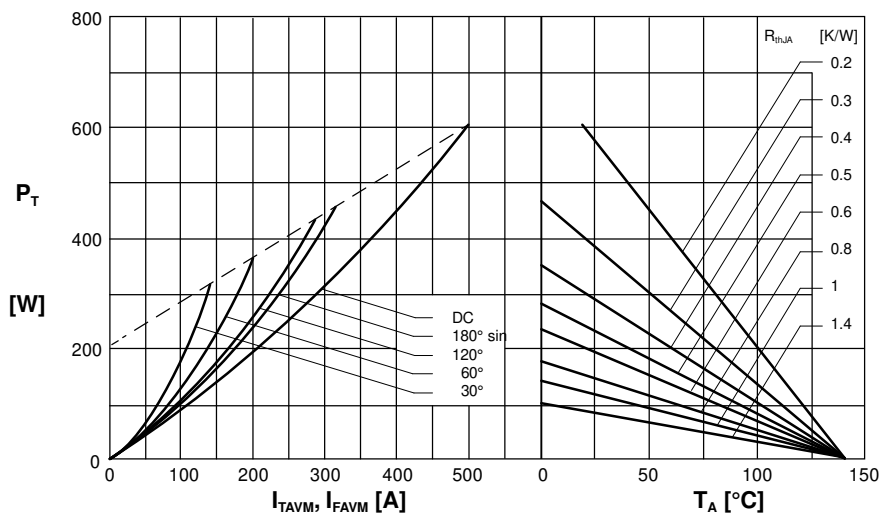


Fig. 4 Power dissipation versus onstate current and
 ambient temperature (per thyristor/diode)



Fig. 5 Gate trigger characteristics

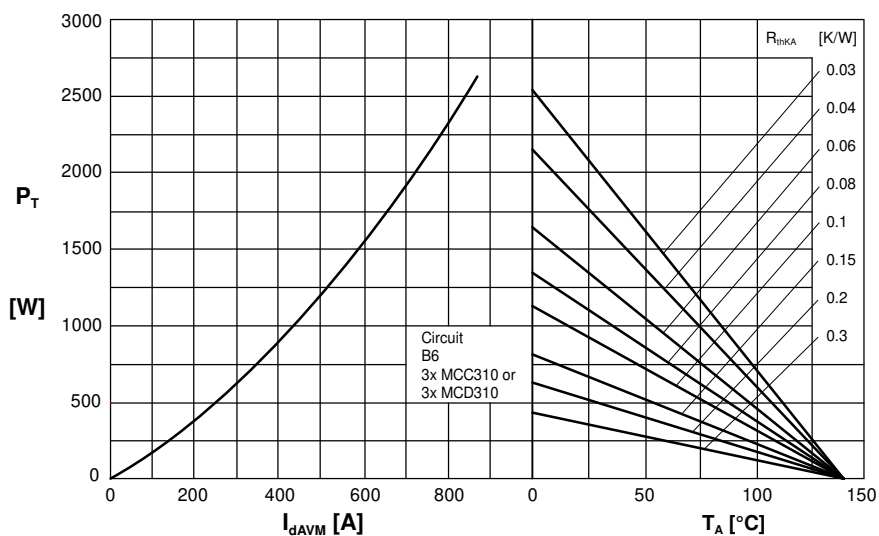


Fig. 6 Three phase rectifier bridge: Power dissipation versus
 direct output current and ambient temperature

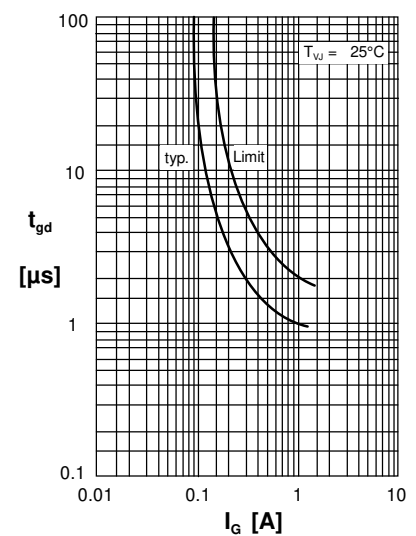


Fig. 7 Gate trigger delay time

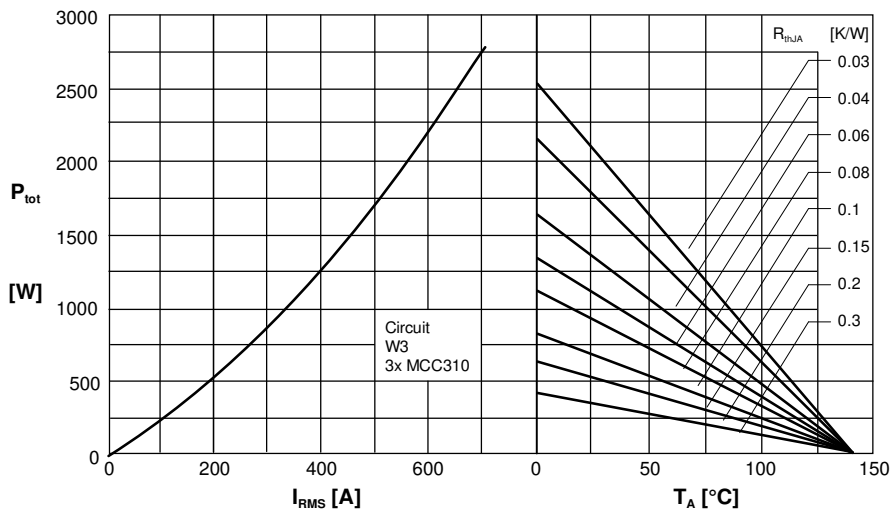
Rectifier


Fig. 7 Three phase AC-controller: •
Power dissipation versus RMS output current and ambient temperature

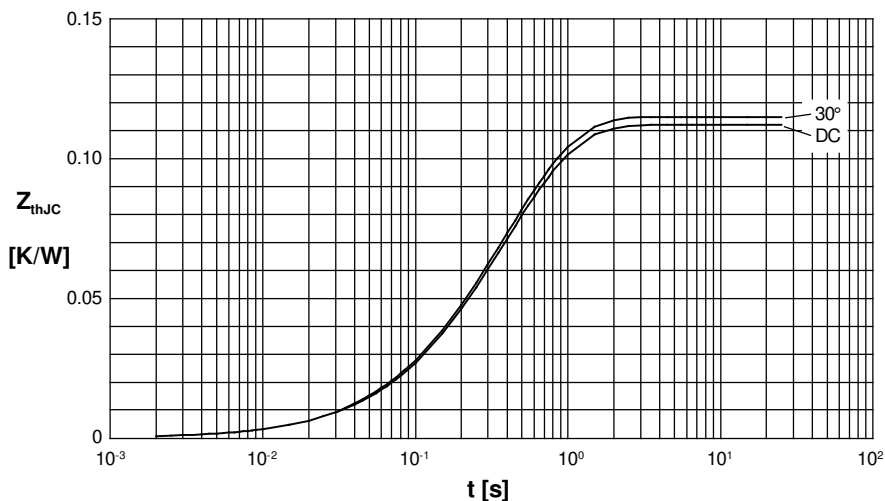


Fig. 8 Transient thermal impedance junction to case (per thyristor)

R_{thJC} for various conduction angles d:

d	R_{thJC} (K/W)
DC	0.112
180°C	0.113
120°C	0.114
60°C	0.115
30°C	0.115

Constants for Z_{thJC} calculation:

i	R_{thi} [K/W]	t_i [s]
1	0.003	0.099
2	0.0143	0.168
3	0.0947	0.456

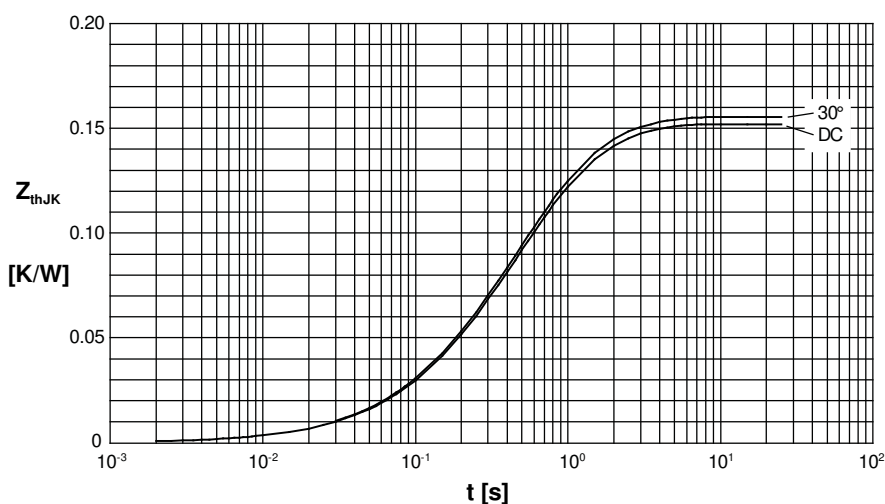


Fig. 9 Transient thermal impedance junction to heatsink (per thyristor)

R_{thJK} for various conduction angles d:

d	R_{thJK} [K/W]
DC	0.152
180°C	0.154
120°C	0.154
60°C	0.155
30°C	0.155

Constants for Z_{thJK} calculation:

i	R_{thi} (K/W)	t_i (s)
1	0.003	0.099
2	0.0143	0.168
3	0.0947	0.456
4	0.04	1.36